UTC UNISONIC TECHNOLOGIES CO.,LTD

MGBR10L45

Preliminary

DIODE

MOS GATED BARRIER RECTIFIER

DESCRIPTION

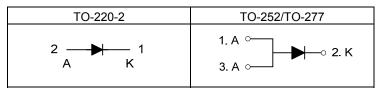
The UTC **MGBR10L45** is a surface mount mos gatedbarrier rectifier, it uses UTC's advanced technology to provide customers withlow forward voltage drop and high switching speed, etc.

FEATURES

* Low forward voltage drop

* High switching speed

SYMBOL

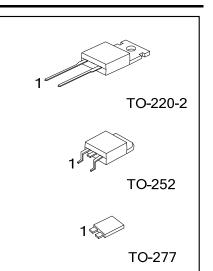


ORDERING INFORMATION

Ordering Number		Deekere	Pin Assignment			Decking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MGBR10L45L-TA2-T	MGBR10L45G-TA2-T	TO-220-2	К	Α	-	Tube	
MGBR10L45L-TN3-T	MGBR10L45G-TN3-T	TO-252	А	К	А	Tube	
MGBR10L45L-TN3-R	MGBR10L45G-TN3-R	TO-252	А	К	А	Tape Reel	
MGBR10L45L-T27-R	MGBR10L45G-T27-R	TO-277	А	К	А	Tape Reel	

Note: Pin Assignment: A: Anode K: Common Cathode

MGBR10L45L- <u>TA2</u> -T	(1) T: Tube, R: Tape Reel			
(2)Package Type	(2) TA2: TO-220-2, TN3: TO-252, T27: TO-277			
(3)Lead Free	(3) L: Lead Free, G: Halogen Free			



■ ABSOLUTE MAXIMUM RATINGS(T_A=25°C, unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load. For capacitance load derate current by 20%.

PARAMETER	SYMBOL	RATINGS	UNIT	
DC Blocking Voltage	V _{RM}	45	V	
WorkingPeak Reverse Voltage	V _{RWM}	45	V	
Peak Repetitive Reverse Voltage	V _{RRM}	45	V	
RMS Reverse Voltage	V _{R(RMS)}	32	V	
Average Rectified Output Current T _c =140°C	Ιo	10	А	
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load	I _{FSM}	90	А	
Repetitive Peak Avalanche Power (1µs, 25°C)	P _{ARM}	5000	W	
Operating Junction Temperature	TJ	-65~+150	°C	
Storage Temperature	T _{STG}	-65~+150	°C	

Note: Absolute maximum ratings are thosevalues beyond which thedevice could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220-2		60	
	TO-252	θ _{JA}	110	°C/W
	TO-277		73 (Note 3)	
	TO-220-2		2	
Junction to Case	TO-252	θ _{JC}	2.5	°C/W
	TO-277		13 (Note 3)	

■ ELECTRICAL CHARACTERISTICS(T_A=25°C,unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	V _{(BR)R}	I _R =0.5mA	45			V
Forward Voltage Drop	V _{FM}	I _F =10A, T _J =25°C			0.58	V
		I _F =10A, T _J =125°C			0.53	V
Leakage Current (Note 1)	DM	V _R =45V, T _J =25°C		50	300	μA
		V _R =45V, T _J =125°C		12	40	mA

Notes: 1. Short duration pulse test used to minimize self-heating effect.

2. Thermal resistance junction to case mounted on heatsink.

3. Mounted on an FR4 PCB, single-sided copper, with 100cm2 copper pad area.



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